Chapter 6

Memory Organization

Outline

- Introduction
- Computer Memory System Overview
 - Characteristics of Memory Systems
 - Memory Hierarchy
- Cache Memory Principles
 - Elements of Cache Design
 - Cache Size
 - Direct Mapping
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 - Write Policy
 - Number of caches
 - Unified versus split caches

- -Cache Addresses
- -Mapping Function
- -Associative Mapping
- -Replacement Algorithms
- -Line Size
- -Multilevel caches

Introduction

A computer has a **hierarchy** of memory subsystems:

- •some internal to the system
 - -i.e. directly accessible by the processor;
- some external
 - accessible via an I/O module;

Computer Memory System Overview

Classification of memory systems according to their key characteristics:

Location

Internal (e.g., processor registers, cache, main memory)

External (e.g., optical disks, magnetic disks, tapes)

Capacity

Number of words

Number of bytes

Unit of Transfer

Word

Block

Access Method

Sequential

Direct

Random

Associative

Performance

Access time

Cycle time

Transfer rate

Physical Type

Semiconductor

Magnetic

Optical

Magneto-optical

Physical Characteristics

Volatile/nonvolatile

Erasable/nonerasable

Organization

Memory modules

Location: either internal or external to the processor.

- Forms of internal memory:
 - registers;
 - cache;
 - and others;
- Forms of external memory:
 - disk;
 - magnetic tape (too old... =P);
 - devices that are accessible to the processor via I/O controllers.

Capacity: amount of information the memory is capable of holding.

- Typically expressed in terms of bytes (1 byte = 8 bits) or words;
- A word represents each addressable block of the memory
 - common word lengths are 8, 16, and 32 bits;
- External memory capacity is typically expressed in terms of bytes;

Unity of transfer: number of bytes read / written into memory at a time.

- Need not equal a word or an addressable unit;
- Also possible to transfer blocks:
 - Much larger units than a word;
 - Used in external memory...
 - External memory is slow...
 - Idea: minimize number of acesses, optimize amount of data transfer;

- Sequential Method: Memory is organized into units of data, called records.
 - Access must be made in a specific linear sequence;
 - Stored addressing information is used to assist in the retrieval process.
 - A shared read-write head is used;
 - The head must be moved from its one location to the another;
 - Passing and rejecting each intermediate record;
 - Highly variable times.

Sequential Method Example: Magnetic Tape



• Direct Access Memory:

- Involves a shared read-write mechanism;
- Individual records have a unique address;
- Requires accessing general record vicinity plus sequential searching, counting, or waiting to reach the final location;
- Access time is also variable;



Magnetic Disk

- Random Access: Each addressable location in memory has a unique,
 - physically wired-in addressing mechanism.
 - Constant time;
 - independent of the sequence of prior accesses;
 - Any location can be selected at random and directly accessed;
 - Main memory and some cache systems are random access.

- Associative: RAM that enables one to make a comparison of desired bit
 - locations within a word for a specified match
 - a word is retrieved based on a portion of its contents rather than its address;
 - retrieval time is constant independent of location or prior access patterns
 - *E.g.*: cache, neural networks.

Performance:



- Access time (latency):
 - For RAM: time to perform a read or write operation;
 - For Non-RAM: time to position the read-write head at desired location;
- **Memory cycle time:** Primarily applied to RAM:
 - Access time + additional time required before a second access;
 - Required for electrical signals to be terminated/regenerated;
 - Concerns the system bus.

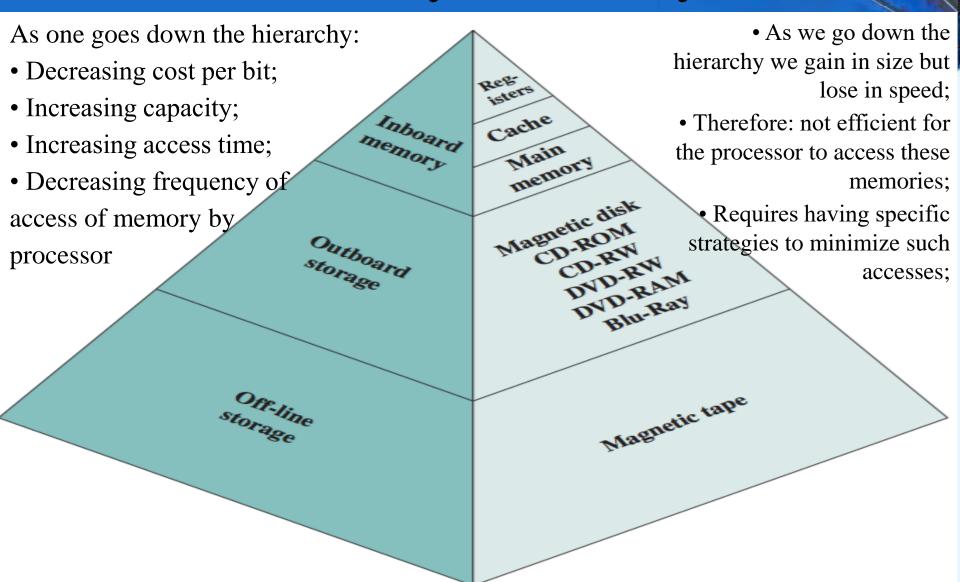
Performance

- Transfer time: Rate at which data can be transferred in / out of memory;
 - For RAM: 1/cycle time
 - For Non-RAM: Tn = TA + n/R where:
 - *Tn*: Average time to read or write n bits;
 - TA: Average access time;
 - n: Number of bits
 - R: Transfer rate, in bits per second (bps)

Physical characteristics:

- Volatile: information decays naturally or is lost when powered off;
- Nonvolatile: information remains without deterioration until changed:
 - no electrical power is needed to retain information.;
 - *E.g.*: Magnetic-surface memories are nonvolatile;
 - Semiconductor memory (memory on integrated circuits) may be either volatile or nonvolatile.

Memory Hierarchy



Key to the success of this organization is the last item:

• Decreasing frequency of access of memory by processor.

Memory Hierarchy

How can we develop strategies to minimize these accesses?

- Space and Time locality of reference principle:
 - Space: if we access a memory location, close by addresses will very likely be accessed;
 - Time: if we access a memory location, we will very likely access it again;

Example....

Suppose that the processor has access to two levels of memory:

- •Level 1 L1: contains 1000 words and has an access time of $0.01 \mu s$;
- •Level 2 L2: contains 100,000 words and has an access time of $0.1 \mu s$.

Assume that:

- If word \in *L*1, then the processor accesses it directly;
- If word \in *L*2, then word is transferred to *L*1 and then accessed by the processor.
- H define the fraction of all memory accesses that are found L1;
- T1 is the access time to L1 0.01μs; and T2 is the access time to L2 0.1μs

Example

- Textual description of the previous :
- For high percentages of L1 access, the average total access time is much closer to that of L1 than that of L2;
- Now lets consider the following scenario:
- Suppose 95% of the memory accesses are found in *L*1. Average time to access a word is:
- $(0.95)(0.01\mu s) + (0.05)(0.01\mu s + 0.1\mu s) = 0.0095 + 0.0055 = 0.015\mu s$
- Average access time is much closer to $0.01\mu s$ than to $0.1\mu s$, as desired.

Strategy to minimize accesses should be:

- organize data across the hierarchy such that
- percentage of accesses to lower levels is substantially less than that of upper levels
- *I.e.* L2 memory contains all program instructions and data:
- Data that is currently being used should be place in *L*1;
- Eventually, data in L1 will have to be swapped back to L2 to make room for new data;
- On average, most references will be to data contained in L1.

This principle can be applied across more than two levels of memory:

- Processor registers:
 - fastest, smallest, and most expensive type of memory
- Followed immediately by the cache:
 - Stages data movement between registers and main memory;
 - Improves perfomance;
 - Is not usually visible to the processor;
 - Is not usually visible to the programmer.
- Followed by main memory:
 - principal internal memory system of the computer; 21
 - Each location has a unique address.

Cache Memory Principles

- Cache memory is designed to combine:
- memory access time of expensive, high-speed memory combined with the large memory size of less expensive, lower-speed memory.
- large and slow memory together with a smaller, faster memory;
- the cache contains a copy of portions of main memory.

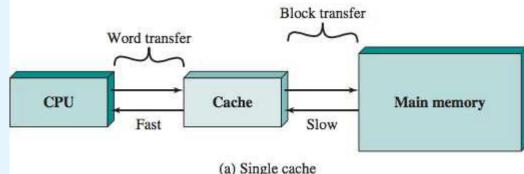


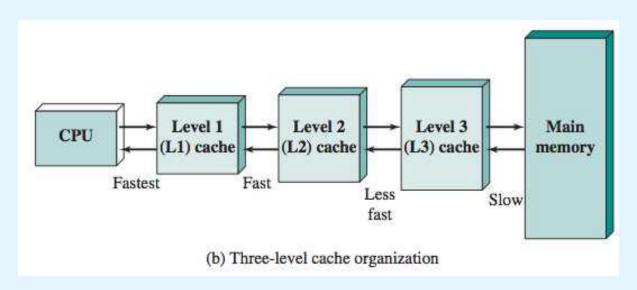
Figure: Cache and main memory - single cache approach (Source: [Stallings, 2015])

Conti.....

- When the processor attempts to read a word of memory: a check is made to determine if the word is in the cache;
- If so, the word is delivered to the processor.
- If the word is not in cache:
 - a block of main memory is read into the cache;
 - then the word is delivered to the processor.
- Because of the locality of reference principle:
- when a block of data is fetched into the cache;
 - it is likely that there will be future references to that same memory location;

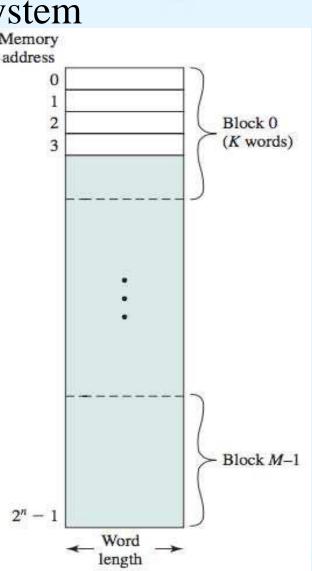
What if we introduce multiple levels of cache?

- L2 cache is slower and typically larger than the L1 cache
- L3 cache is slower and typically larger than the L2 cache.



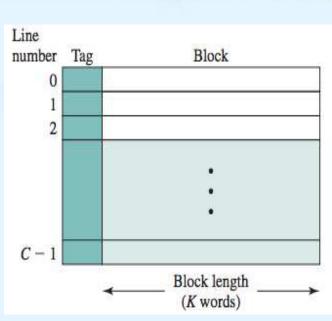
Main memory:

- the structure of the main-memory system
 - Consists of 2^n addressable words;
 - Each word has a unique *n*-bit address;
 - Memory consists of a number of fixed words each;
 - There are $M = 2^n/K$ blocks;
 - Where:
 - M is total number of blocks,
 - n is the number of bits is a word
 - K is the number of words in a block

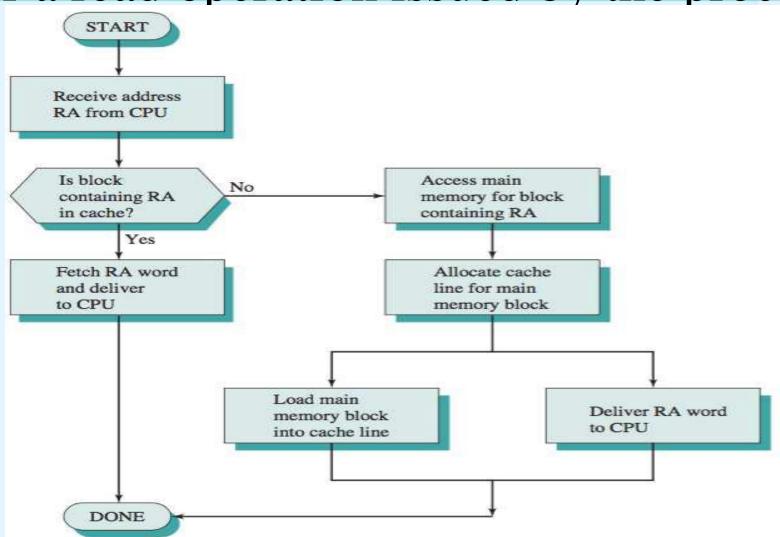


Conti...

- the structure of the cache system
 - Consisting of *m* blocks, called lines;
 - Each line contains *K* words;
 - $-m \ll M$
 - Each line also includes control bits:
 - Not shown in the figure;
 - If a word in a block of memory is read:
 - block is transferred to a cache line; because $m \ll M$, lines: cannot permanently store a block.
 - need to identify the block stored;
 - info stored in the tag field;



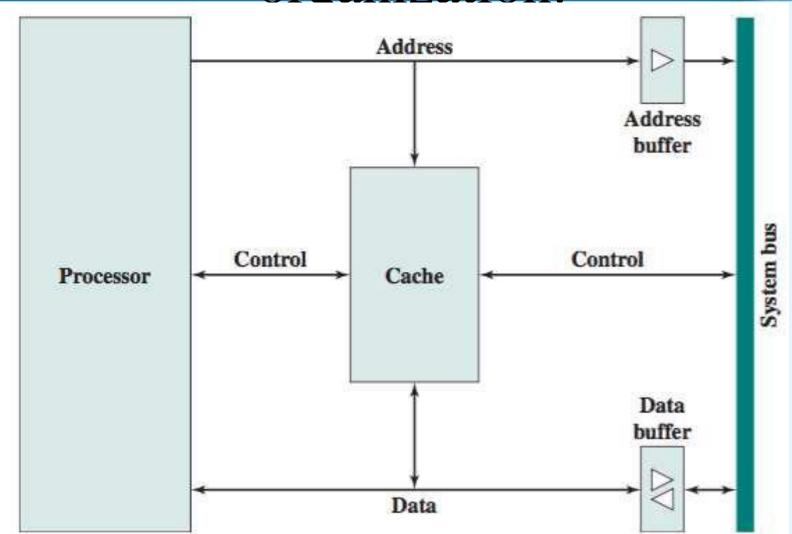
Set of operations that need to be performed for a read operation issued by the processor



Cache Read operation:

- Processor generates **read address** (**RA**) of word to be read;
- If the word ∈ cache, it is delivered to the processor;
- Otherwise:
 - Block containing that word is loaded into the cache from RAM;
 - Word is delivered to the processor;
 - These last two operations occurring in parallel.

Typical contemporary cache organization:



Cont...

- In this organization the cache:
- connects to the processor via data, control, and address lines; the data and address lines also attach to data and address buffers:
- which attach to a system bus.....from which main memory is reached.
- What do you think happens when a word is **in** cache? When a **cache hit** occurs (word is in cache):
 - the data and address buffers are disabled;
 - communication is only between processor and cache;
 - no system bus traffic.

Cont...

- What do you think happens when a word is not in cache?
 - When a cache miss occurs (word is not in cache):
 - the desired address is loaded onto the system bus;
 - the data are returned through the data buffer...to
 both the cache and the processor

Elements of Cache Design: Cache architectures can be classified according to key elements:

Cache Addresses

Logical

Physical

Cache Size

Mapping Function

Direct

Associative

Set associative

Replacement Algorithm

Least recently used (LRU)

First in first out (FIFO)

Least frequently used (LFU)

Random

Write Policy

Write through

Write back

Line Size

Number of Caches

Single or two level

Unified or split

Cache memory Organization

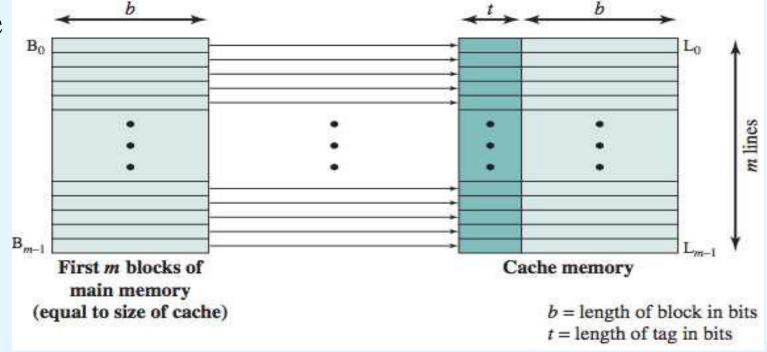
Mapping Function

- Recall that there are fewer cache lines than main memory blocks
- How should one map main memory blocks into cache lines?
- Three techniques can be used for mapping blocks into cache lines:
 - direct;
 - associative;
 - set associative

Direct Mapping

- Maps each block of main memory into only one possible cache line as: $i = j \mod m$
- where: i = cache line number; j = main memory block number; and m = number of lines in the

cache



Conti...

- Previous picture shows mapping of main memory blocks into cache:
- First *m* main memory blocks map into each line of the cache;
- Next *m* blocks of main memory map in the following manner:
 - Bm maps into line L0 of cache;
 - -Bm+1 maps into line L1;
 - and so on...
- Modulo operation implies repetitive structure;

Conti....

With direct mapping blocks are assigned to lines

as follows:

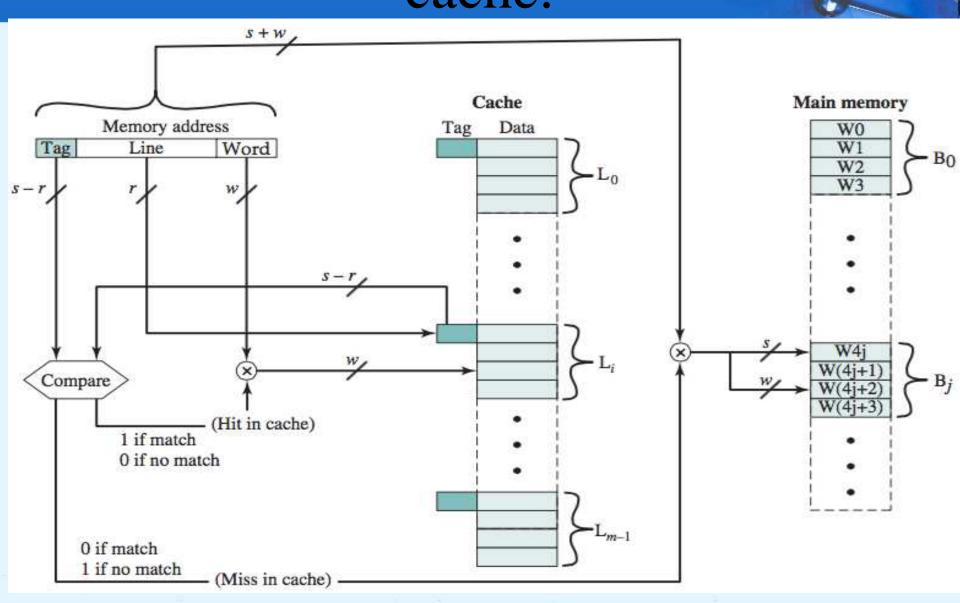
Cache line	Main memory blocks assigned
0	$0, m, 2m, \ldots, 2^s - m$
1	$1, m + 1, 2m + 1, \ldots, 2^s - m + 1$
m - 1	$m-1,2m-1,3m-1,\ldots,2^s-1$

• Over time:

- each line can have a different main memory block;
- we need the ability to distinguish between these;
- the most significant s r bits (tag) serve this purpose.

- Each main **memory address** (s + w bits) can be viewed as:
- **Offset** (*w* bits): identifies a word within a block of main memory;
- Line (r bits): specify one of the 2^r cache lines;
- Tag (s r) bits): to distinguish blocks that are mapped to the same line:
- Note that:
 - s allows addressing of all blocks in main memory... whilst the number of available cache lines is much smaller than 2^s
 - Tag fields identifies the block that is currently mapped to a cache line;

To determine whether a block is in the cache:



To determine whether a block is in the cache:

- 1 Use the line field of the memory address to index the cache line;
- 2 Compare the tag from the memory address with the line tag;
- 1 If both match, then Cache Hit:
 - 1 Use the line field of the memory address to index the cache line;
 - 2 Retrieve the corresponding word from the cache line;
- 2 If both do not match, then Cache Miss:
 - 1 Use the line field of the memory address to index the cache line;
 - 2 Update the cache line (word + tag);

Direct mapping technique:

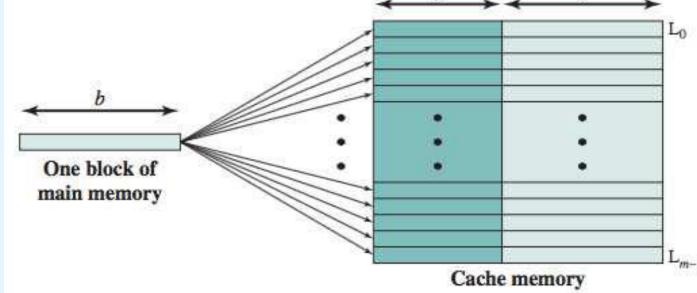
- Advantage: simple and inexpensive to implement;
- **Disadvantage:** there is a fixed cache location for any given block;
- if a program happens to reference words repeatedly from two different blocks that map into the same line;
- then the blocks will be continually swapped in the cache;
- hit ratio will be low (a.k.a. **thrashing**).

Associative Mapping

Overcomes the disadvantage of direct mapping by:

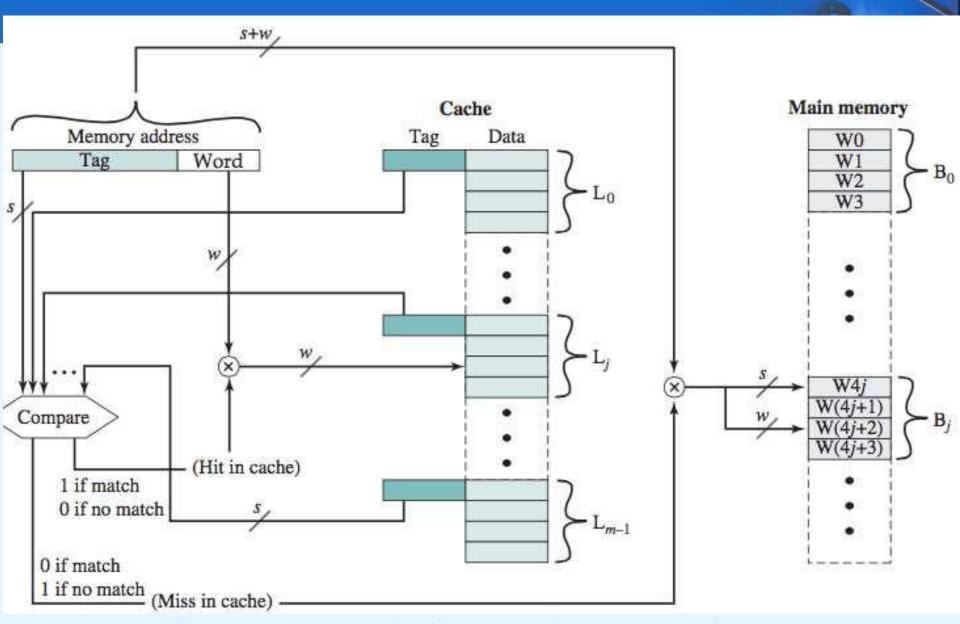
• permitting each block to be loaded into any cache

line:



- Cache interprets a memory address as a Tag and a Word field:
- **Tag:** (s bits) uniquely identifies a block of main memory;
- Word: (w bits) uniquely identifies a word within a block;

Fully associative cache organization



To determine whether a block is in the cache:

- Simultaneously **compare** every line's tag for a match:
- If a match exists, then Cache Hit:
 - 1 Use the tag field of the memory address to index the cache line;
 - 2 Retrieve the corresponding word from the cache line;
- If a match does not exist, then Cache Miss:
 - 1 Choose a cache line. How?
 - **2** Update the cache line (word + tag);

Advantage and Disadvantage of Associative mapping technique:

- Advantage: flexibility as to which block to replace when a new block is read into the cache;
- **Disadvantage:** complex circuitry required to examine the tags of all cache lines in parallel.

Can you see any way of improving this scheme?

Perform less comparisons

- Instead of comparing the tag against all lines
- compare only against a subset of the cache lines.
- Welcome to set-associative mapping =)

Set-associative mapping

Combination of direct and associative approaches:

- Cache consists of a number of sets, each consisting of a number of lines.
- From direct mapping:
 - each block can only be mapped into a single set;
 - *I.e.* Block Bj always maps to set j;
 - Done in a modulo way =)
- From associative mapping:
 - each block can be mapped into any cache line of a certain set.



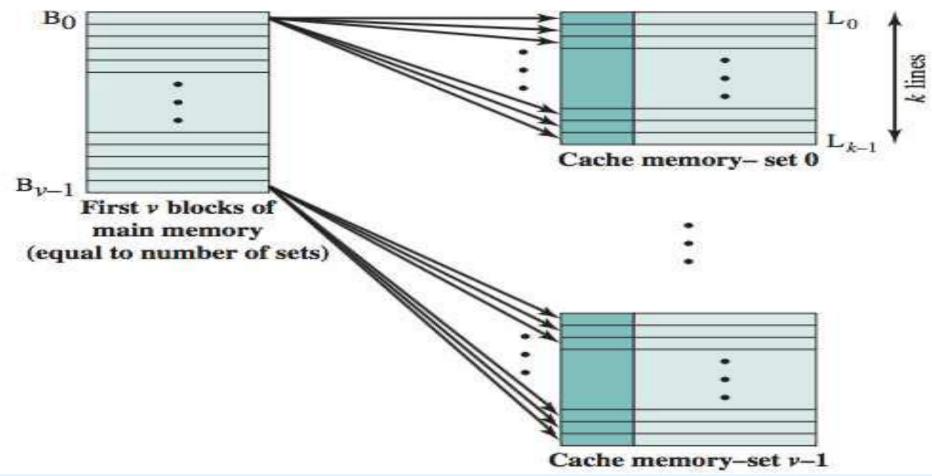
The relationships are:

- $m = v \times k$
- $i = j \mod v$

where:

- -i = cache set number;
- j = main memory block number;
- m = number of lines in the cache;
- v = number of sets;
- k = number of lines in each set

Associative Mapped



Idea:

- 1 memory block!1 single set, but to any row of that set.
- can be physically implemented as *v* associative caches

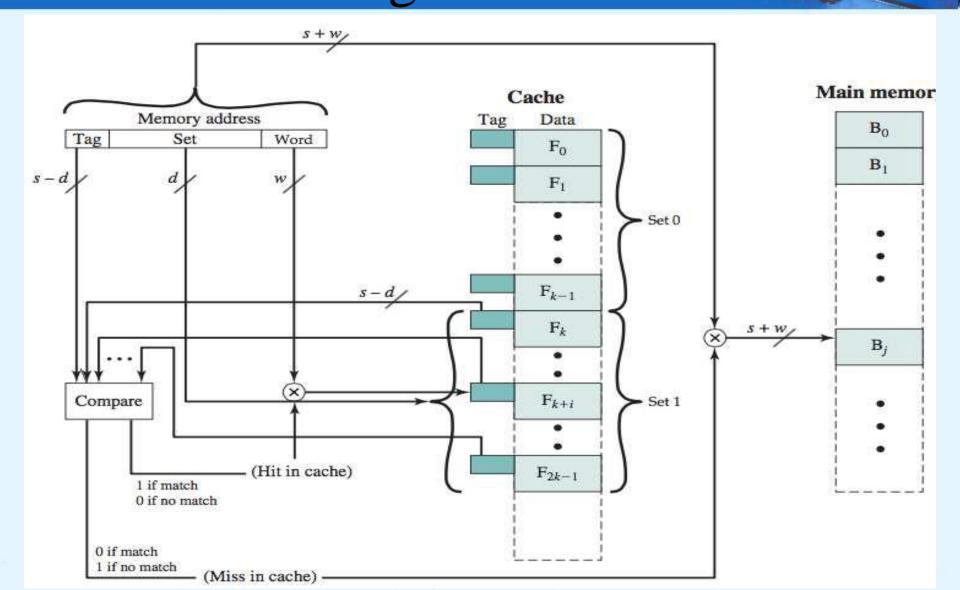
Cache interprets a memory address as a **Tag**, a **Set** and a **Word** field:

- Set: identifies a set (d bits, v = 2d sets);
- **Tag:** used in conjunction with the set bits to identify a block (s d bits);
- Word: identifies a word within a block;

To determine whether a block is in the cache:

- 1 Determine the set through the set fields;
- 2 Compare address tag simultaneously with all cache line tags;
- 3 If a match exists, then Cache Hit:
 - 1 Retrieve the corresponding word from the cache line;
- 4 If a match does not exist, then Cache Miss:
 - 1 Choose a cache line within the set. How?
 - 2 Update the cache line (word + tag);

K-Way Set Associative Cache Organization



Number of caches

Recent computer systems:

use multiple caches;

This design issue covers the following topics

- number of cache levels;
- also, the use of unified versus split caches;

Lets have a look at the details of each one of these...

Multilevel Caches

As logic density increased:

- became possible to have a cache on the same chip as the processor:
 - reduces the processor's external bus activity;
 - therefore improving performance;
- when the requested instruction or data is found in the on-chip cache:
 - bus access is eliminated;
 - because of the short data paths internal to the processor:
 - cache accesses will be faster than even zero-wait state bus cycles.
 - Furthermore, during this period the bus is free to support other transfers.

With the continued shrinkage of processor components:

- processors now incorporate a second cache level (L2) or more:
- savings depend on the hit rates in both the L1 and L2 caches.
 - In general: use of a second-level cache does improve performance;
 - However, multilevel caches complicate design issues:
 - size;
 - replacement algorithms;
 - write policy;

Unified versus split caches

In recent computer systems:

- it has become common to **split** the cache into two:
 - Instruction cache;
 - Data cache;
- both exist at the same level:
 - typically as two L1 caches:
 - When the processor attempts to fetch:
 - an instruction from main memory, it first consults the instruction L1 cache,
 - data from main memory, it first consults the data L1 cache.

Two potential advantages of a unified cache:

- Higher hit rate than split caches:
 - automatically load balancing between instruction and data fetches, i.e.:
 - if an execution pattern involves more instruction fetches than data fetches...the cache will tend to fill up with instructions;
 - if an execution pattern involves relatively more data fetches...the cache will tend to fill up with data;
- Only one cache needs to be designed and implemented.

Key advantage of the split cache design:

- eliminates competition for the cache between
 - Instruction fetch/decode/execution stages...
 - and the load / store data stages;
- Important in any design that relies on the **pipelining** of instructions:
 - fetch instructions ahead of time
 - thus filling a pipeline with instructions to be executed.



With a unified instruction / data cache:

- Data / instructions will be stored in a single location;
- Pipelining:
 - allows for multiples stages of the instruction cycle to be executed simultaneously.
- Because there is a single cache:
 - The executions of multiple stages cannot be performed;
 - Performance bottleneck;

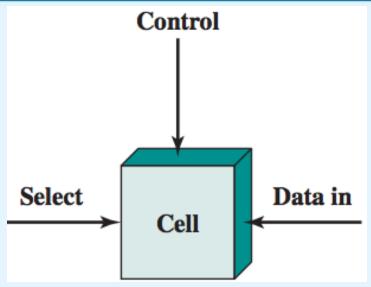
Split cache structure overcomes this difficulty.

Semiconductor Main Memory

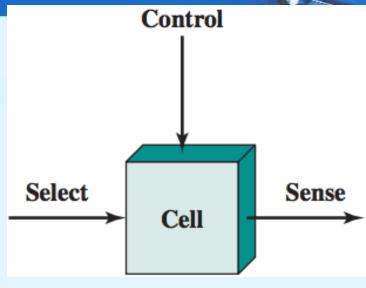
Memory is a collection of **cells** with the following properties

- They exhibit two stable states, used to represent binary 1 and 0;
- They are capable of being written into (at least once), to set the state;
- They are capable of being read to sense the state;
- Access time is the same regardless of the location;

- Cell has three terminals capable of carrying an electrical signal:
- **select:** selects a memory cell for a read / write operation;
- **control:** indicates whether a read / write operation is being performed;
- read/write:
 - For writing, terminal sets the state of the cell to 1 or 0.
 - For reading, terminal is used for output of the cell's state.



Memory cell write operation



Memory cell read operation

Example Consider, a memory with a capacity of 1K words of 16 bits each:

- Capacity:
 - $1K \times 16 = 16Kbits = 2Kbytes$;
- Each word has an address: 0 to 1023
- When a word is read or written:
 - memory acts on all 16 bits;

Contents of a 1024 x 16 Memory

Memory Address				
Binary	Decimal	Memory Contents		
0000000000 0		10110101 01011100		
0000000001 1		10101011 10001001		
000000010	2	00001101 01000110		
	•			
	•			
	•	•		
	•	•		
	•	•		
1111111101	1021	1021 10011101 00010101		
1111111110	1022	00001101 00011110		
1111111111	1023	11011110 00100100		

Write operation steps:

- 1 Apply the binary address of the desired word to the address lines.
- 2 Apply the data bits that must be stored in memory to the data input lines.
- 3 Activate the Write control line.
- Memory unit will then transfer the bits to that address.

Read operation steps:

- 1 Apply the binary address of the desired word to the address lines.
- 2 Activate the Read control line.
- 3 Memory unit will then transfer the bits to the data output lines.

Memory unit operation is controlled by an external device :

- CPU is synchronized by its own clock pulses;
- Memory, however, does not employ a clock:
 - control signals are employed for read / write.
 - Access time time required for specifying an address and obtaining the word;
 - Write time time required for specifying an address and storing the word;
 - CPU must provide the control signals synchronized with its clock:
 - This implies that:
 - read / write operations will take a certain number of clock periods;
 - What does this mean? Lets see with an example =)

Example



Assume:

- CPU with a clock frequency of 50 Mhz;
- Memory access time: 65ns;
- Memory write time: 75ns
- How many clock pulses do we need for read / write operations?

Conti...



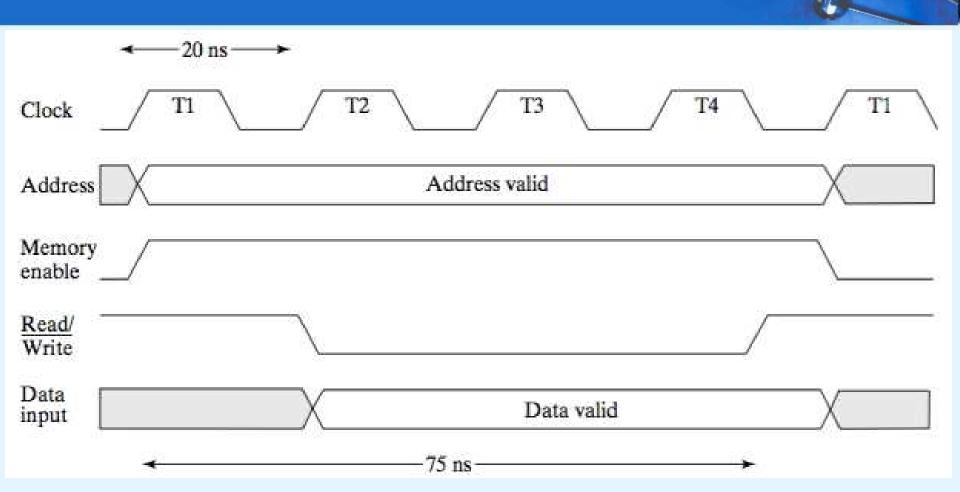
- CPU with a clock frequency of 50 Mhz:
- How long does one clock pulse take? Any Ideas?
- f=1/p
- p = 1/f
- p = 1/50Mhz
- $p = 1/50 \times 10^6 hz$
- $p = 2 \times 10^{-8} s = 20 ns$

- CPU clock pulse: 20ns;
- Assume:
 - Memory access time: 65ns;
 - Memory write time: 75ns

How many clock pulses do we need for read / write operations?

• 4 clock pulses for read / write operations;

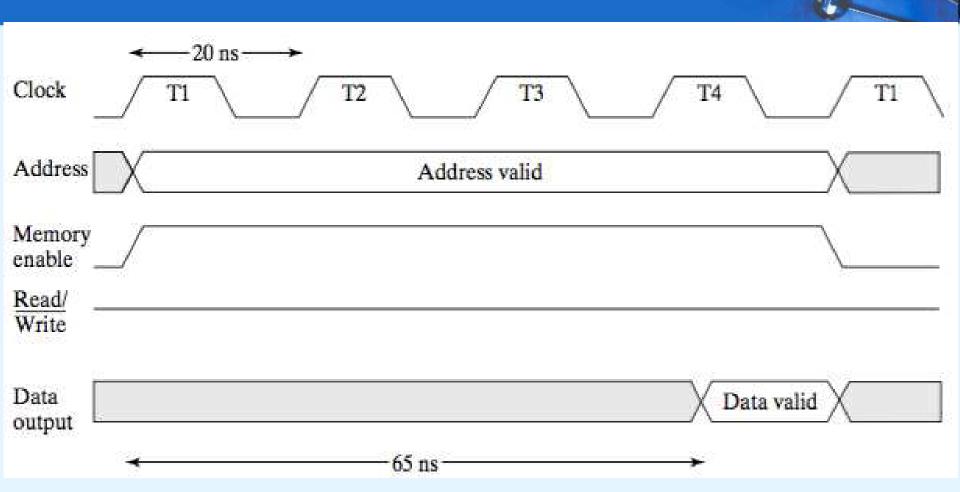
write operation



write operation:

- 1 CPU must provide the address (T1 pulse);
- 2 Memory enable is set (T1 pulse);
- 3 Data is supplied (T2 pulse);
- 4 Read/Write signal set to 0 for write operation (T2 pulse):
 - CPU waits for T2 to let the address signals stabilize:
 - Otherwise: wrong address may be used!
 - Signal must stay activated long enough for the operation to finish;
- 5 When T4 completes, write operation has ended with 5ns to spare

read operation:



read operation:

- 1 CPU must provide the address (T1 pulse);
- 2 Memory enable is set (T1 pulse);
- 3 Read/Write signal set to 1 for read operation (T2 pulse):
 - Signal must stay activated long enough for the operation to finish;
 - Selected word is placed onto the data output lines;
- **4** When T4 completes, write operation has ended with 15ns to spare

Major types of semiconductor memory

Memory Type	Category	Erasure	Write Mechanism	Volatility
Random-access memory (RAM)	Read-write memory	Electrically, byte-level	Electrically	Volatile
Read-only memory (ROM)	Read-only memory	Not possible	Masks	
Programmable ROM (PROM)			Electrically	Nonvolatile
Erasable PROM (EPROM)	Read-mostly memory	UV light, chip-level		
Electrically Erasable PROM (EEPROM)		Electrically, byte-level		
Flash memory		Electrically, block-level		

Random-access memory

- Randomly access any possible address;
- Possible both to read and write data;
- Volatile: requires a power supply;
- For a chip with m words with n bits per word:
 - Consists of an array with $m \times n$ binary storage cells
- *E.g.*: DRAM and SRAM.
 - Lets have a look at these =)

Dynamic RAM (DRAM)

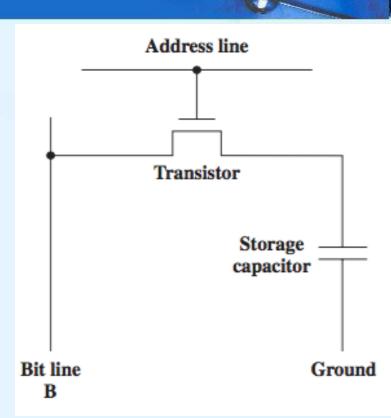
Made with **cells** that store data as charge on capacitors:

- Capacitor charge presence or absence is interpreted as a binary 1 or 0;
- Capacitors have a natural tendency to discharge;
- Requires periodic charge refreshing to maintain data storage

DRAM Cell components:

If voltage goes to the address line:

- Transistor closes:
- Current flows to capacitor;
- If **no** voltage goes to the address line:
- Transistor opens:
- No current flows to capacitor;

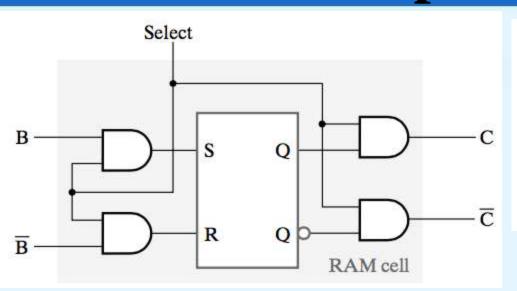


Static RAM (SRAM)



- Remember flip-flops? We saw them at the beginning of the semester...
- Same logic elements used in the processor registers;
- will hold its data as long as power is supplied to it.

Cell storage is modeled by an SR flip-flop:



S	R	\mathbf{Q}_{n+1}
0	0	\mathbf{Q}_n
0	1	0
1	0	1
1	1	_

SR Flip flop table

SRAM Cell

- Flip-flop **inputs** are enabled by a **select** (S) signal:
 - S = 0, stored content is held;
 - S = 1, stored content is determined by B and B'
- Flip-flop outputs are enabled by a select (S) signal:
 - S = 0, both C and C are 0;
 - S = 1, C is the stored value and C' is its complement.

Pros / Cons of DRAM and SRAM

- Both are volatile: power must be continuously supplied to preserve the bit values;
- DRAMs: Periodically refresh capacitor's charge;
- SRAM: No need to periodically refresh;
- DRAM cell is simpler and smaller than a SRAM cell: (1 transistor, 1 capacitor) vs. SR flip-flop
- DRAM is denser (smaller cells = more cells per unit area);
- Due to its simplicity: DRAM is cheaper than corresponding SRAM;

- DRAM requires the supporting refresh circuitry (readout):
 - This is a fixed cost, does not increase with size =)
 - This cost is more than compensated by the smaller cost of DRAM cells;
 - Thus, DRAMs tend to be favored for large memory requirements;
- SRAMs are faster and more expensive than DRAMs
 - No need to refresh the circuitry after a readout;
- Because of these characteristics:
 - **DRAM:** used in main memory; & **SRAM:** used in cache;

Memory technology	Typical access time	\$ per GiB in 2012
SRAM semiconductor memory	0.5–2.5 ns	\$500-\$1000
DRAM semiconductor memory	50–70 ns	\$10–\$20
Flash semiconductor memory	5,000-50,000 ns	\$0.75-\$1.00
Magnetic disk	5,000,000–20,000,000 ns	\$0.05-\$0.10

Read-only memory (ROM)

- Contains a permanent pattern of data that cannot be changed;
 - Therefore:
 - Possible to read a ROM;
 - Not possible to write data more than once;
- Advantage:
 - Data / Program is permanently in main memory;
 - No need to load from a secondary storage device;
 - Original BIOS were stored in ROM chips.
- Nonvolatile: no power source is required;



- Data is wired into the chip as part of the fabrication process
- Data insertion is expensive;
- No room for error:
 - If one bit is wrong, the whole batch of ROMs must be thrown out.

Different types of ROM Programmable ROM (PROM):

- nonvolatile and may be written into only once;
- Writing may be performed at a later time than the original chip fabrication.
- Special equipment is required for the writing process;
- More expensive than ROM;

Erasable programmable read-only memory (EPROM):

- Can be altered multiple times;
- Entire memory contents need to be erased;
- Special equipment is required for the erasure process:
 Ultra-violet radiation;
- Slow erasure procedure (>20 minutes); & More expensive than PROM;

Electrically erasable programmable read-only memory (EEPROM):

- Can be altered multiple times;
- Special equipment is required for the erasure process:
 - No need to erase prior contents...only the byte or bytes addressed are updated.
 - Ultra-violet radiation;
- Faster erasure procedure than EPROM;
- More expensive than EPROM;

Flash memory:

- named because of the speed with which it can be reprogrammed;
- between EPROM and EEPROM in both cost and functionality:
 - Uses an electrical erasing technology;
 - Possible to erase blocks of memory;
 - Does not provide byte-level erasure;
- Technology used in pendrives;